Vishay Siliconix

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

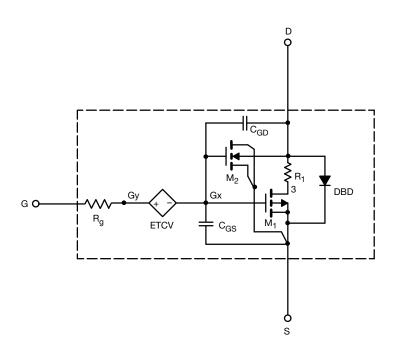
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A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- Apply for both linear and switching application
- Accurate over the -55 °C to +125 °C temperature range
- Model the gate charge

SUBCIRCUIT MODEL SCHEMATIC



Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits

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| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | |
|--|---------------------|---|-------------------|------------------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS | SIMULATED DATA | MEASURED DATA | UNIT |
| Static | | | | | |
| Gate-source threshold voltage | V _{GS(th)} | $V_{DS}=V_{GS},\ I_{D}=-250\ \mu A$ | 2.1 | - | V |
| Drain-source on-state resistance ^a | R _{DS(on)} | $V_{GS} = -10 \text{ V}, \text{ I}_{D} = -6 \text{ A}$ | 0.0079 | 0.0076 | Ω |
| | | $V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -5 \text{ A}$ | 0.0126 | 0.0120 | |
| Forward transconductance ^a | g fs | $V_{DS} = -15 \text{ V}, \text{ I}_{D} = -6 \text{ A}$ | 29 | 32 | S |
| Diode forward voltage | V _{SD} | I _S = -6 A | -0.78 | -0.78 | V |
| Dynamic ^b | | | | | |
| Input capacitance | C _{iss} | V_{DS} = -25 V, V_{GS} = 0 V, f = 1 MHz | 4100 | 3620 | pF |
| Output capacitance | C _{oss} | | 368 | 360 | |
| Reverse transfer capacitance | C _{rss} | | 355 | 346 | |
| Total gate charge | Qg | V_{DS} = -25 V, V_{GS} = -10 V, I_D = -5 A | 62 | 65 | nC |
| Gate-source charge | Q _{gs} | | 9 | 9 | |
| Gate-drain charge | Q _{gd} | | 12 | 12 | |

Notes

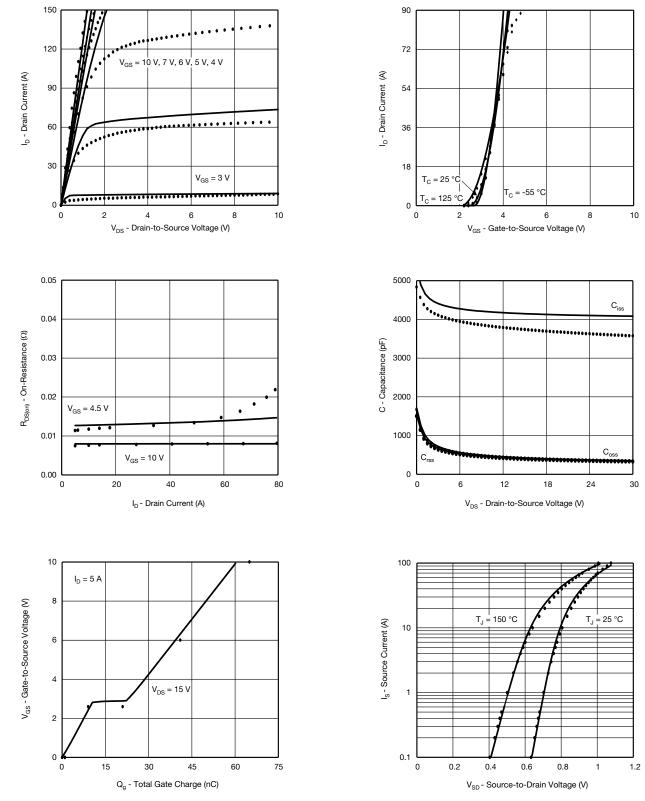
a. Pulse test; pulse width $\leq 300~\mu\text{s},\,duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing



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COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)



Note

• Dots and squares represent measured data Copyright: Vishay Intertechnology, Inc.

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